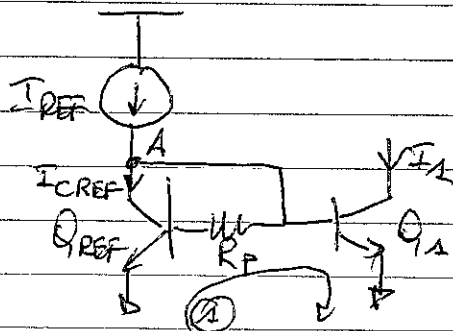


## HW4 Solutions

Problem 1

$$I_1 = 1.1 I_{1, \text{nom}} \quad ? R_P$$

First, compute  $I_{1, \text{nom}}$ , i.e.  $I_1$  with  $R_P = 0$

$$I_{1, \text{nom}} = I_{\text{REF}} \cdot \frac{1}{1 + \frac{2}{\beta}}$$

$$\Rightarrow I_1 = 1.1 I_{\text{REF}} \cdot \frac{1}{1 + \frac{2}{\beta}}$$

Now, let's consider  $R_P$ :

$$\text{KVL @ LOOP ①: } V_{\text{BE, REF}} + \frac{I_{\text{CREF}}}{\beta} R_P = V_{\text{BE, 1}}$$

$$V_T \ln\left(\frac{I_1}{I_S}\right) - V_T \ln\left(\frac{I_{\text{CREF}}}{I_S}\right) = \frac{I_{\text{CREF}}}{\beta} R_P$$

$$R_P = \frac{\beta}{I_{\text{CREF}}} V_T \ln\left(\frac{1.1 I_{\text{REF}} \cdot \frac{1}{1 + \frac{2}{\beta}}}{I_{\text{CREF}}}\right) \quad (1)$$

$$\text{KCL @ A: } I_{\text{REF}} = I_{\text{CREF}} + \frac{I_{\text{CREF}}}{\beta} + \frac{I_1}{\beta}$$

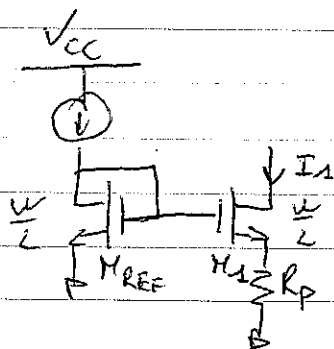
$$I_{\text{CREF}} = \frac{I_{\text{REF}} \left(1 - \frac{1.1}{\beta \left(1 + \frac{2}{\beta}\right)}\right)}{1 + \frac{1}{\beta}} = \frac{\beta(\beta + 0.9)}{(\beta + 1)(\beta + 2)} I_{\text{REF}}$$

Now substitute back in (1)

$$R_p = \frac{(\beta+1)(\beta+2)}{\beta+0.9} \frac{V_T}{I_{REF}} \ln \left[ \frac{1 + \beta(\beta+1)(\beta+2)}{\beta(\beta+2)(\beta+0.9)} \right]$$

$$\Rightarrow R_p = \frac{(\beta+1)(\beta+2)}{\beta+0.9} \frac{V_T}{I_{REF}} \ln \left[ \frac{1 + \beta(\beta+1)}{\beta+0.9} \right]$$

## Problem 2



?  $R_p$  s.t.  $I_1 = \frac{I_{REF}}{2}$

$$V_{GS, REF} = V_{TH} + \sqrt{\frac{2I_{REF}}{K_n \frac{w}{L}}}$$

KVL:  $V_{GS1} = V_{GS, REF} - I_1 R_p$

$$\Rightarrow V_{GS1} = V_{TH} + \sqrt{\frac{2I_{REF}}{K_n \frac{w}{L}}} - \frac{I_{REF}}{2} R_p$$

$$(*) \quad I_1 = \frac{1}{2} K_n \frac{w}{L} \left[ \sqrt{\frac{2I_{REF}}{K_n \frac{w}{L}}} - \frac{I_{REF}}{2} R_p \right]^2 = \frac{I_{REF}}{2}$$

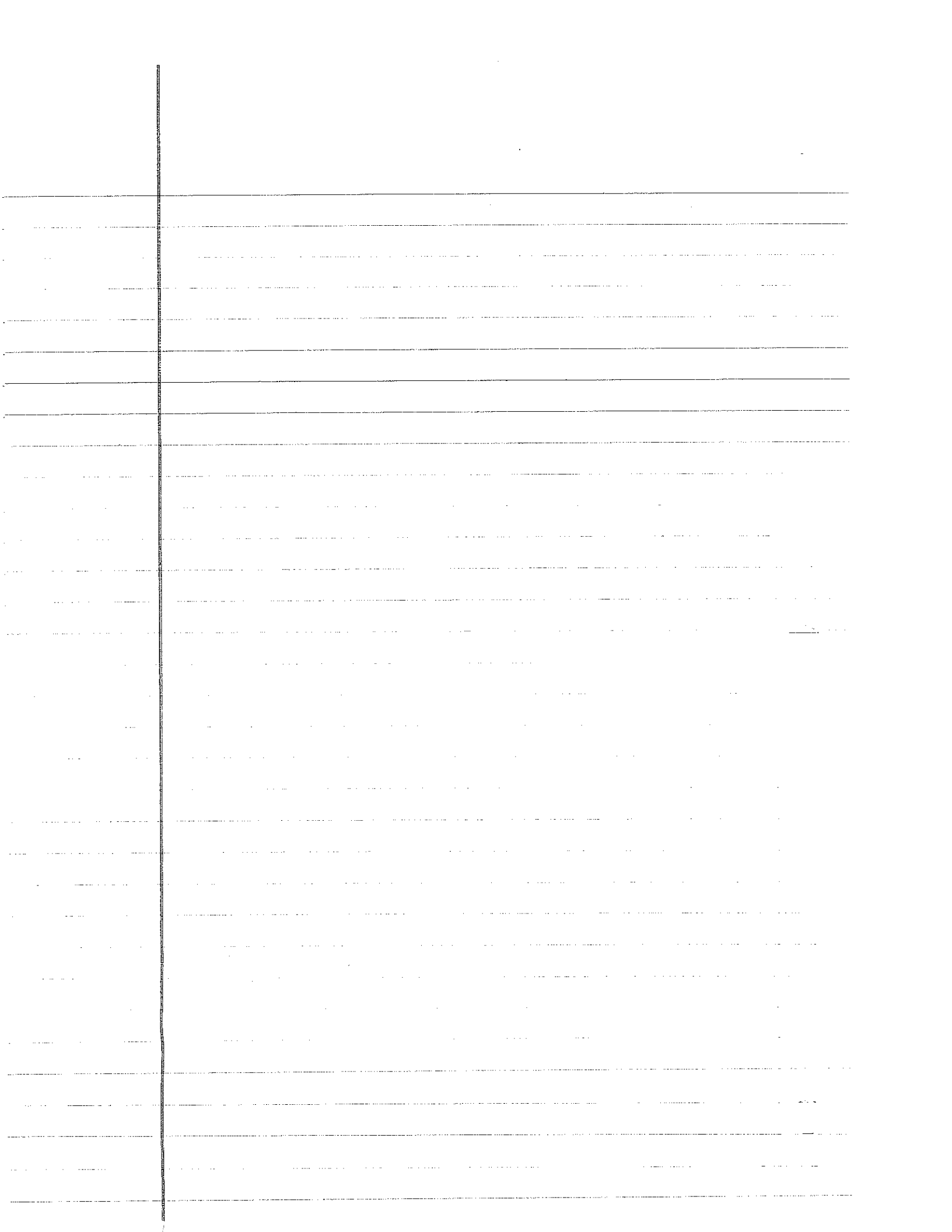
$$\sqrt{\frac{2I_{REF}}{K_n \frac{w}{L}}} - \frac{I_{REF}}{2} R_p = \sqrt{\frac{2 \cdot I_{REF}/2}{K_n \frac{w}{L}}}$$

$$\frac{I_{REF}}{2} R_p = \sqrt{\frac{2I_{REF}}{K_n \frac{w}{L}}} - \sqrt{\frac{I_{REF}}{K_n \frac{w}{L}}} \quad \frac{I_{REF}}{2} R_p = (\sqrt{2} - 1) \sqrt{\frac{I_{REF}}{K_n \frac{w}{L}}}$$

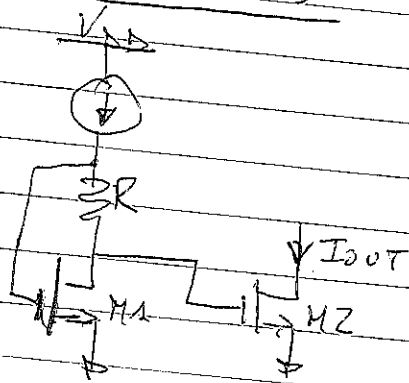
$$R_p = \frac{2(\sqrt{2} - 1)}{\sqrt{I_{REF}} K_n \frac{w}{L}}$$

$I_1$  does not change if the threshold voltage of the transistors change by the same amount  $\Delta V$ .

Looking at expression (\*), we can see that there is no dependence on  $V_{TH}$  (because the  $V_{TH}$  of the two transistors cancel out).



### Problem 3



$$I_{OUT} = 0.1 \mu A \quad \left(\frac{W}{L}\right)_1 = \left(\frac{W}{L}\right)_2$$

Part a) Given  $I_{IN} = 1 \mu A$   
determine the range of  $\frac{W}{L}_1$  s.t. M1 operates in saturation (strong inversion).

We need to determine the ~~value~~ range of  $\left(\frac{W}{L}\right)_1$  and for each value of  $\left(\frac{W}{L}\right)_1$  compute the corresponding value of R that guarantees an output current of  $I_{OUT} = 0.1 \mu A$

From G8M 4.4.1.4

$$I_{OUT} = \frac{K'}{2} \left(\frac{W}{L}\right)_1 \left[ \sqrt{\frac{2I_{IN}}{K' \frac{W}{L}}} - R I_{IN} \right]^2 \quad (*)$$

solving for R

$$R = \frac{\sqrt{\frac{2I_{IN}}{K' \frac{W}{L}}} - \sqrt{\frac{2I_{OUT}}{K' \frac{W}{L}}}}{I_{IN}}$$

To operate in strong inversion:

$$V_{OV1} = \sqrt{\frac{2I_{IN}}{K' \frac{W}{L}}} \geq 2n V_T = 78 \text{ mV}$$

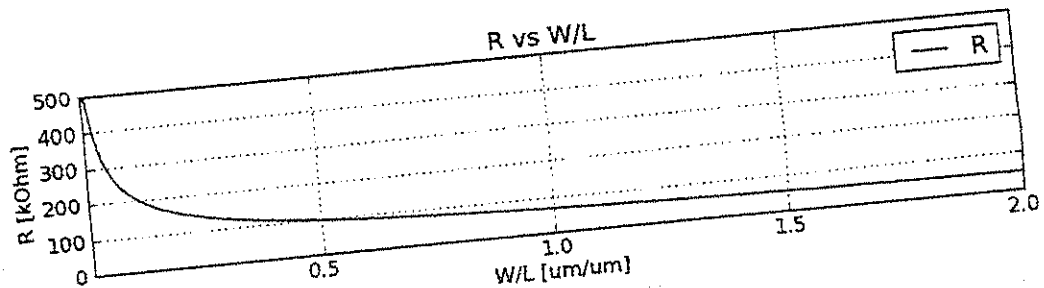
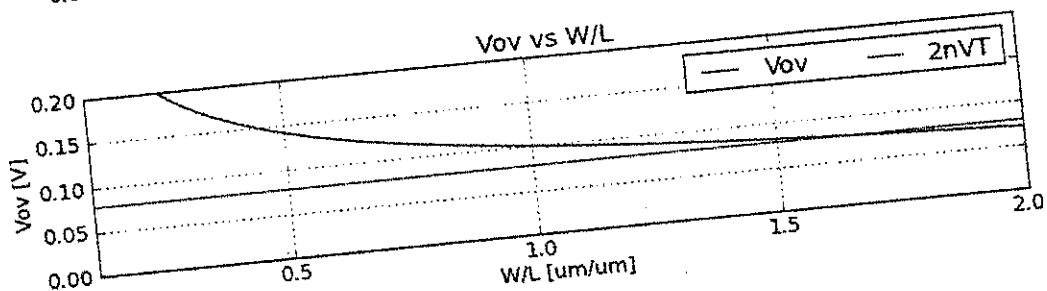
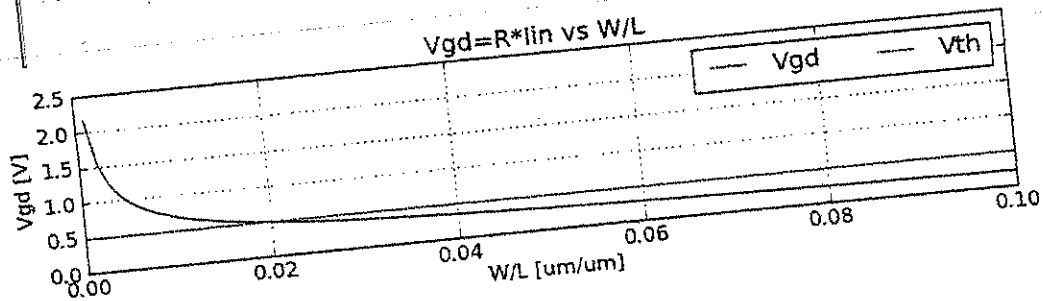
To operate in saturation:

$$V_{GS1} = R I_{IN} \leq V_{TH} = 0.5 \text{ V}$$

We can now sweep  $\frac{W}{L}$  and determine the range of values that satisfy the above conditions. For low  $\frac{W}{L}$  a bigger  $R$  will be required to obtain the desired  $I_{out}$ , so we can compute  $\left(\frac{W}{L}\right)_{min}$  to maintain saturation. For high  $\frac{W}{L}$ , the  $V_{ov}$  of  $M_1$  will keep on decreasing until entering weak inversion. The plot below shows the trend of the quantities of interest. We get the limits

$$0.018 \leq \frac{W}{L} \leq 1.643$$

$$496k\Omega \geq R \geq 53k\Omega$$

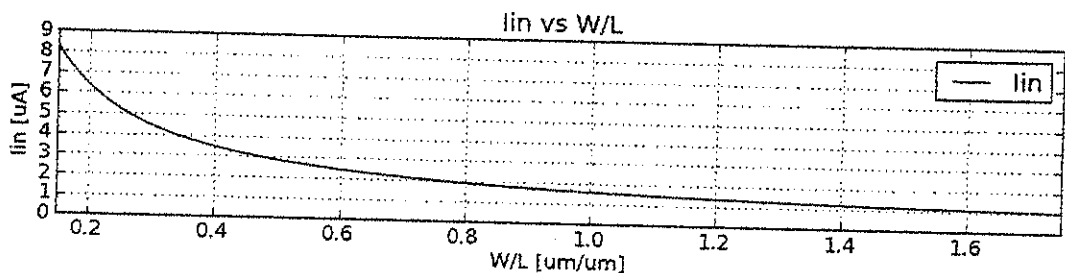
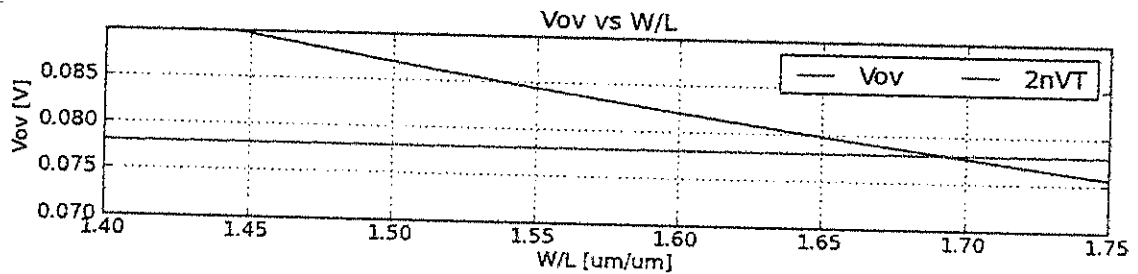
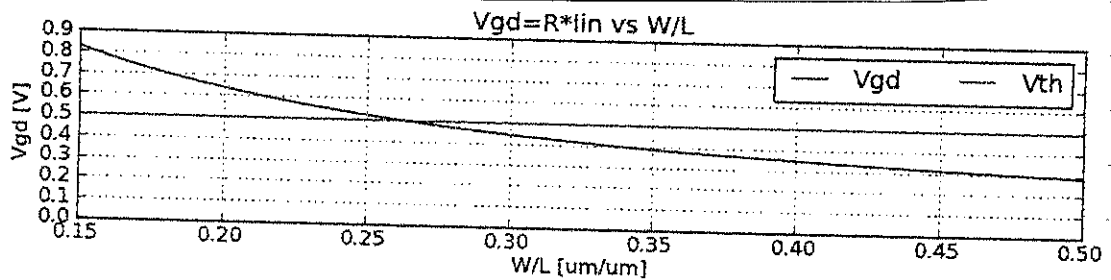


Part 8) Now fix  $R = 100 \text{ k}\Omega$  and compute the range of  $\frac{W}{L}$  and  $I_{in}$  to maintain  $\frac{V}{L}$  in strong inversion and saturation.

We use the same constraints as before but now solve Equation (\*) numerically for simplicity. We get the following ranges:

$$0.262 \leq \frac{W}{L} \leq 1.691$$

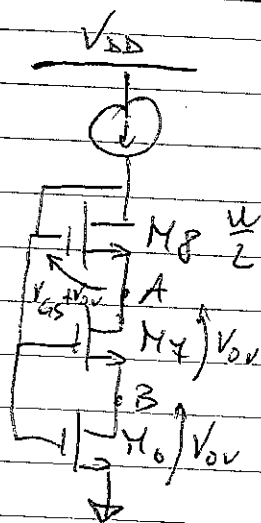
$$5 \mu\text{A} \leq I_{in} \leq 1.028 \mu\text{A}$$



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# Problem 4



Determine  $\left(\frac{W}{L}\right)_{M6}$ ,  $\left(\frac{W}{L}\right)_{M7}$  such that

$$V_{DSH6} = V_{DSH7} = V_{OVH8}$$

$M_8$  is diode connected, so it operates in saturation. Further, the circuit connection forces  $M_4$  and  $M_6$  to operate in triode because  $V_{GSH6} > V_{GSH4} > V_{TH}$  when  $M_8$  is on.

$$\text{KCL @ A: } \frac{K'}{2} \left(\frac{W}{L}\right)_8 (V_{GS8} - V_T)^2 = \frac{K'}{2} \left(\frac{W}{L}\right)_7 [2(V_{GS7} - V_T)V_{DS7} - V_{DS7}^2]$$

$$\text{we now enforce } V_{DS7} = V_{OV8} \quad V_{GS8} = V_T + V_{OV}$$

$$\Rightarrow V_{GS7} = V_{GS8} + V_{DS7} = V_T + 2V_{OV}$$

$$\Rightarrow \frac{K'}{2} \left(\frac{W}{L}\right)_8 V_{OV}^2 = \frac{K'}{2} \left(\frac{W}{L}\right)_7 [2(2V_{OV})V_{OV} - V_{OV}^2]$$

$$\Rightarrow \boxed{\left(\frac{W}{L}\right)_7 = \frac{1}{3} \left(\frac{W}{L}\right)_8}$$

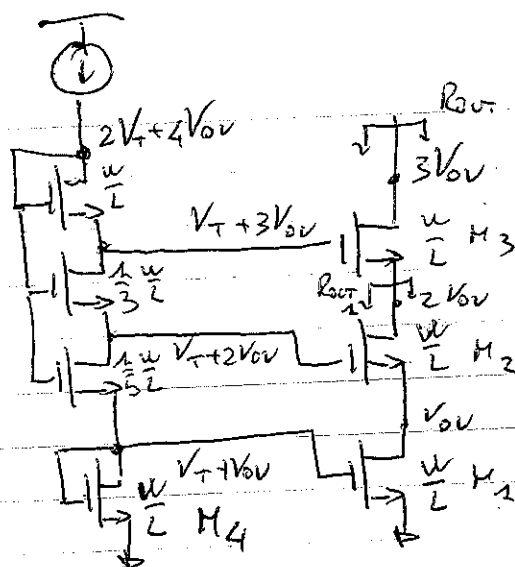
$$\text{KCL @ B: } \frac{K'}{2} \left(\frac{W}{L}\right)_8 (V_{GS8} - V_T)^2 = \frac{K'}{2} \left(\frac{W}{L}\right)_6 [2(V_{GS6} - V_T)V_{DS6} - V_{DS6}^2]$$

$$\text{we have: } V_{DS8} = V_{OV8} \quad V_{GS8} = V_T + V_{OV}$$

$$V_{GS6} = V_{GS8} + V_{DS7} + V_{DS6} = V_T + 3V_{OV}$$

$$\Rightarrow \frac{K'}{2} \left(\frac{W}{L}\right)_8 V_{OV}^2 = \frac{K'}{2} \left(\frac{W}{L}\right)_6 [2(3V_{OV})V_{OV} - V_{OV}^2]$$

$$\Rightarrow \boxed{\left(\frac{W}{L}\right)_6 = \frac{1}{5} \left(\frac{W}{L}\right)_8}$$



The transistor sizes are the ones reported on the schematic.

$$R_{OUT1} = r_{o1} + r_{o2} + g_{m2} r_{o1} r_{o2}$$

$$R_{OUT} = r_{o3} + R_{OUT1} + g_{m3} r_{o3} R_{OUT1} \approx g_m^2 r_o^3$$

The minimum output voltage to operate all transistors in saturation is  $3V_{OV}$ .

The voltage of all nodes in the input branch have been reported on the schematic

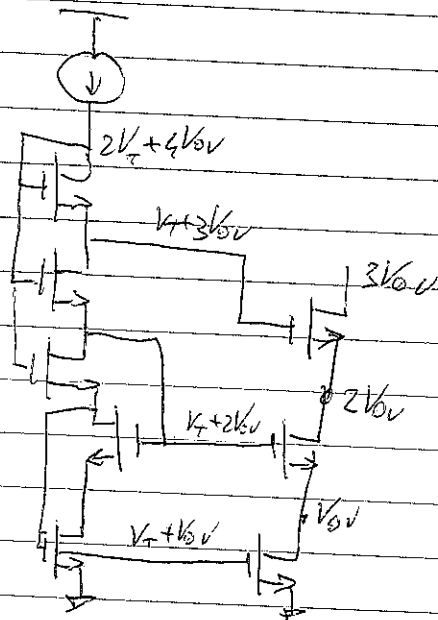
The systematic error is due to the difference in  $V_{DS}$  between transistors  $M1$  and  $M4$ .

Assuming a linear dependence of the output current of an MOS in saturation with  $V_{DS}$ , we get

$$\epsilon = \frac{V_{DS1} - V_{DS4}}{V_A} \approx \frac{V_{OV1} - (V_T + V_{OV3})}{V_A} \approx -\frac{V_T}{V_A}$$

The error is negative because there is less current flowing in the output branch.

Using Sodi cascode Topology, we get:



$$\xi = 0$$

